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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	10/082,997
				Filing Date	February 25, 2002
				First Named Inventor:	Steven N. Towle
				Art Unit	1753
				Examiner Name	McDonald, Rodney Glenn
Sheet	1	of 1		Attorney Docket Number	42390P5783D
NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published			T ²
		ANNEN, A., ET AL., Erosion of amorphous hydrogenated boron-carbon thin films, Journal of Nuclear Materials 231 (1996) pgs. 151-154, © 1996 Elsevier Science, B.V.			
		ENDO, KAZUHIKO, ET AL., Fluorinated amorphous carbon thin films grown by helicon plasma enhanced chemical vapor deposition for low dielectric constant interlayer dielectrics, Appl. Phys. Lett. 68 (20) 13 May 1996, pgs. 2864-2866, © American Institute of Physics.			
		ENDO, KAZUHIKO, ET AL., Fluorinated amorphous carbon thin films grown by plasma enhanced chemical vapor deposition for low dielectric constant interlayer dielectrics, J. Appl. Phys. 78 (2), 15 July 1995, pgs. 1370-1372, © 1995 American Institute of Physics.			
		ENDO, KAZUHIKO, ET AL., Nitrogen doped fluorinated amorphous carbon thin films grown by plasma enhanced chemical vapor deposition for low dielectric constant interlayer dielectrics, Appl. Phys. Lett. 68 (25), 17 June 1996, pgs. 3656-3658 © 1996 American Institute of Physics.			
		MATSUBARA, Y., ET AL., Low-k Fluorinated Amorphous Carbon Interlayer Technology for Quarter Micron Devices, ULSI Device Development Labs, *Microelectronic Res. Labs., **VLSI Manufacturing Engineering Division, NEC Corporation, 1120 Shimokuzawa, Sagamihara, Kanagawa, 229, Japan, 4 pages, No Date.			
		SHARAPOV, V.M., ET AL., Erosion of a-B/C : H films under deuterium plasma irradiation, Journal of Nuclear Materials 220-222 (1995) 930-933, pgs. 930-933, © 1995 Elsevier Science B.V.			
		YAMAKI, T., ET AL., Thermal desorption spectroscopy of boron/carbon films after keV deuterium irradiation, Journal of Nuclear Materials 217 (1994) 154-160, pgs. 154-160, © 1994 Elsevier Science B.V.			

Examiner Signature		Date Considered	3/3/04
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*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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